MRF1000MB

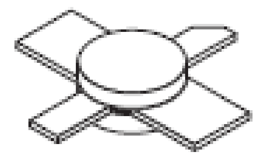
Class A, Class AB Microwave Power Silicon NPN Transistor
0.7 W, 960–1215 MHz, 18V

Rev. V1

Features

- Guaranteed performance @ 1090 MHz, 18 Vdc — Class A
- Output power: 0.2W
- Minimum gain: 10dB
- 100% tested for load mismatch at all phase angles with 10:1 VSWR
- Industry standard package
- Nitride passivated
- Gold metallized, emitter ballasted for long life and resistance to metal migration
- Internal input matching for broadband operation

Product Image



CASE 332A–03, STYLE 2

Description and Applications

Designed for Class A and AB common emitter amplifier applications in the low–power stages of IFF, DME, TACAN, radar transmitters, and CW systems.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	20	Vdc
Collector–Base Voltage	V_{CBO}	50	Vdc
Emitter–Base Voltage	V_{EBO}	3.5	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ T_C = 25°C (1) Derate above 25°C	P_D	7.0 40	Watts mW/°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (2)	$R_{\theta JC}$	25	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I_C = 5.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector–Emitter Breakdown Voltage (I_C = 5.0 mAdc, V_{BE} = 0)	$V_{(BR)CES}$	50	—	—	Vdc
Collector–Base Breakdown Voltage (I_C = 5.0 mAdc, I_E = 0)	$V_{(BR)CBO}$	50	—	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 1.0 mAdc, I_C = 0)	$V_{(BR)EBO}$	3.5	—	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)	I_{CBO}	—	—	0.5	mAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	10	—	100	—

1. These devices are designed for RF operation. The total device dissipation rating applies only when the device is operated as RF amplifiers.
2. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

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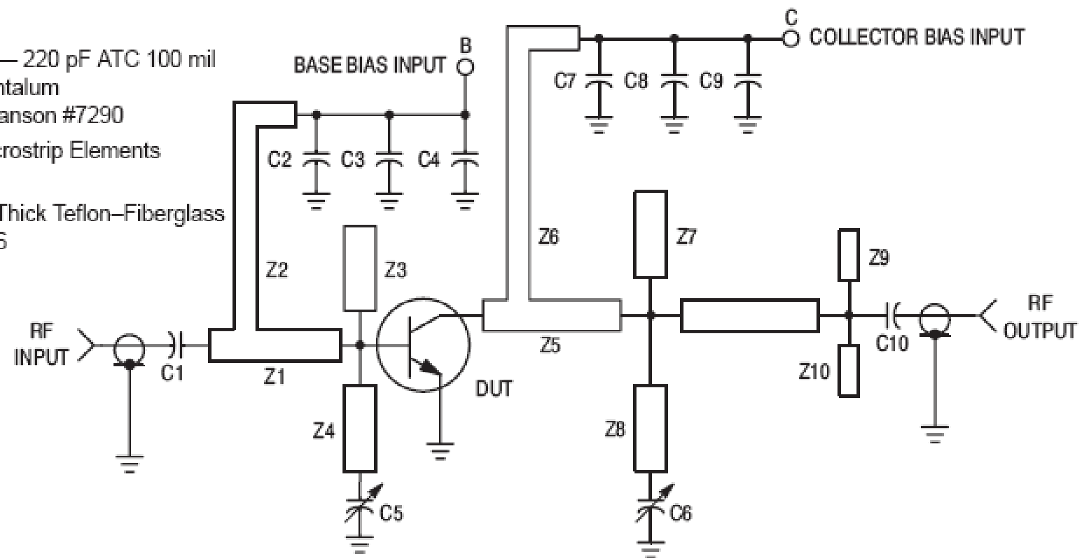
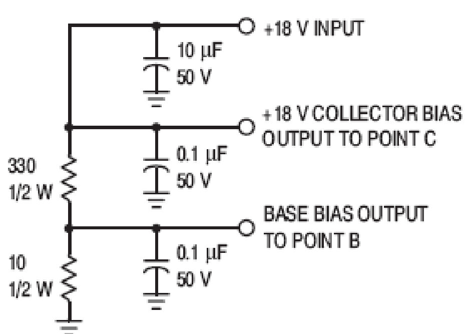
ELECTRICAL CHARACTERISTICS — continued (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS					
Output Capacitance (V_{CB} = 28 Vdc, I_E = 0, f = 1.0 MHz)	C_{ob}	—	2.0	5.0	pF
FUNCTIONAL TESTS					
Common–Emitter Power Gain — Class A (V_{CE} = 18 Vdc, I_C = 100 mAdc, f = 1090 MHz, P_{out} = 200 mW)	G_{PE}	10	12	—	dB
Common–Emitter Power Gain — Class AB (V_{CE} = 18 Vdc, I_{CQ} = 10 mAdc, f = 1090 MHz, P_{out} = 0.7 W)	G_{PE}	—	10.7	—	dB
Load Mismatch — Class A (V_{CE} = 18 Vdc, I_C = 100 mAdc, f = 1090 MHz, P_{out} = 200 mW, VSWR = 10:1 All Phase Angles)	ψ	No Degradation in Power Output			

C1, C2, C3, C7, C8, C10 — 220 pF ATC 100 mil
C4, C9 — 4.7 μF 50 V Tantalum
C5, C6 — 0.8–8.0 pF Johanson #7290
Z1–Z10 — Distributed Microstrip Elements — See Figure 8
Board Material — 0.031″ Thick Teflon–Fiberglass ε_r = 2.56



Class AB Bias Control Circuit
18 V Output I_{CQ} 10 mA Nominal



Class A Constant Current Bias Control Circuit
I_C = 100 mA, V_{CE} = 18 V

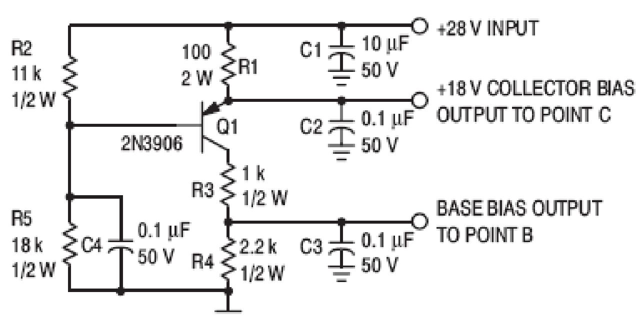


Figure 1. 1090 MHz Test Circuit

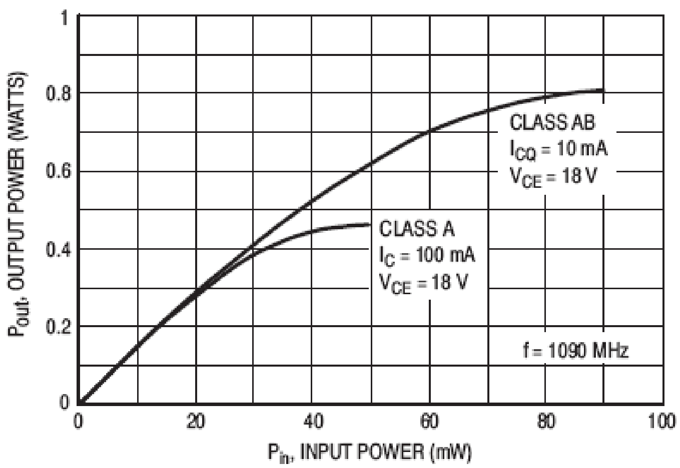


Figure 2. Output Power versus Input Power

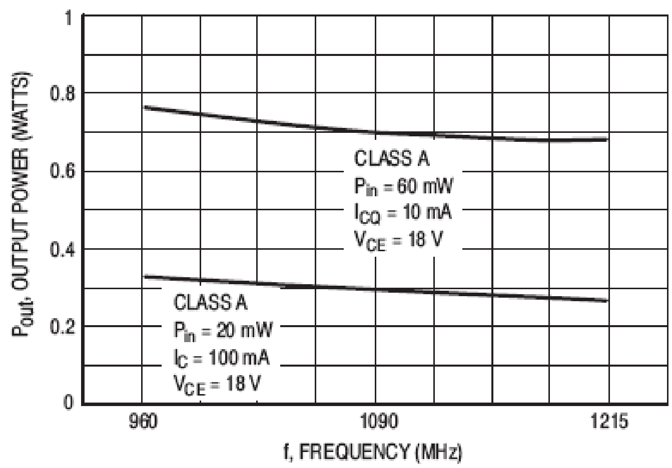


Figure 3. Output Power versus Frequency

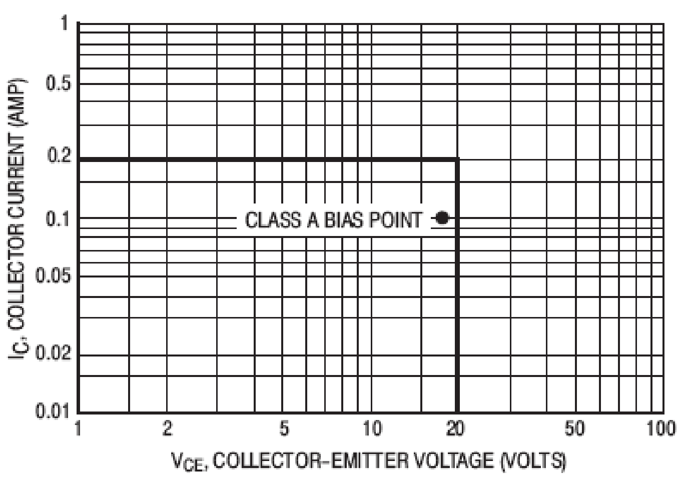


Figure 4. DC Safe Operating Area

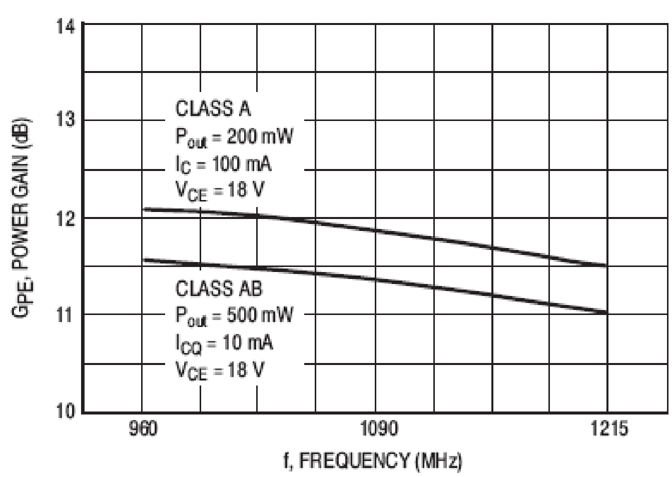


Figure 5. Power Gain versus Frequency

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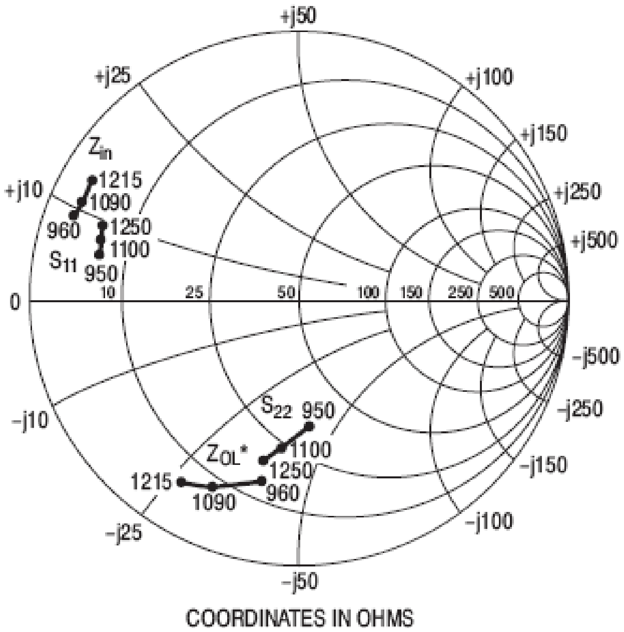


SERIES EQUIVALENT IMPEDANCES
P_{out} = 0.5 W, V_{CE} = 18 Vdc,
I_{CQ} = 10 mAdc, Class AB

f MHz	Z_{in} Ohms	Z_{OL}* Ohms
960	3.0 + j9.0	16 – j40
1090	3.2 + j10	8.5 – j31
1215	2.8 + j12	7.0 – j26

Z_{OL}* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage, and frequency.

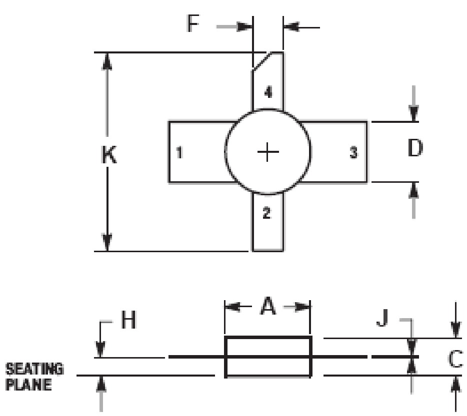
S–PARAMETERS — V_{CE} = 18 Vdc, I_C = 100 mAdc, Class A

f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
	$\lvert S_{11}\rvert$	∠ φ	$\lvert S_{21}\rvert$	∠ φ	$\lvert S_{12}\rvert$	∠ φ	$\lvert S_{22}\rvert$	∠ φ
950	0.77	166	2.42	40	0.016	42	0.48	–87
1000	0.78	165	2.36	38	0.016	48	0.50	–90
1050	0.77	163	2.31	33	0.016	46	0.51	–94
1100	0.77	162	2.31	28	0.016	46	0.54	–97
1150	0.78	161	2.20	23	0.015	46	0.57	–100
1200	0.78	159	2.20	19	0.016	47	0.59	–103
1250	0.78	158	2.12	12	0.016	42	0.61	–106

Figure 6. Common–Emitter S–Parameters and Series Equivalent Input/Output Impedances

Replaces MRF1000MA/D

PACKAGE DIMENSIONS



STYLE 2:
PIN 1. EMITTER
2. BASE
3. EMITTER
4. COLLECTOR

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.270	0.290	6.86	7.36
C	0.115	0.135	2.93	3.42
D	0.195	0.205	4.96	5.20
F	0.095	0.105	2.42	2.66
H	0.050	0.070	1.27	1.77
J	0.003	0.007	0.08	0.17
K	0.600	---	15.24	---

CASE 332A–03
ISSUE D